

**APT15DQ120BG**  
**Datasheet**  
**Ultrafast Soft Recovery Rectifier Diode**

Final  
October 2018



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# 1 Revision History

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The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

## 1.1 Revision E

Revision E was published in October 2018. The following is a summary of the changes in revision E of this document.

- Product image was updated.
- Product features were updated. For information, see [Product Overview \(see page 2\)](#).
- The lead thickness in the package outline drawing was updated. For more information, see [Package Outline Drawing \(see page 9\)](#).

## 1.2 Revision D

Revision D was published in May 2011. The following is a summary of the changes in revision D of this document.

- Patent information was removed.
- Maximum lead thickness was changed from 0.79 mm (0.031 in.) to 1.016 mm (0.040 in.).

## 1.3 Revision C

Revision C was published in October 2006. The following is a summary of the changes in revision C of this document.

- The datasheet template was updated.
- Thermal ladder was updated.

## 1.4 Revision B

Revision B was published in August 2005.  $I_{RM}$  was changed to 100  $\mu$ A, 1000 V and above.

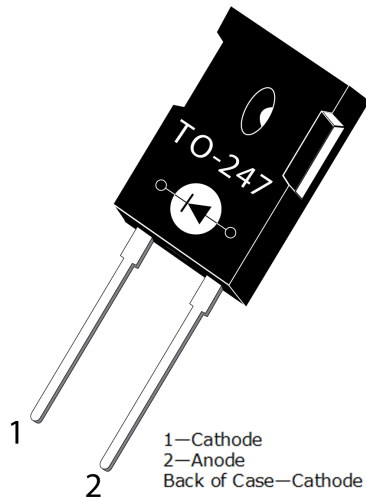
## 1.5 Revision A

Revision A was published in May 2005. It is the first publication of this document.

## 2 Product Overview

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This section outlines the product overview for the APT15DQ120BG device.



### 2.1 Features

The following are key features of the APT15DQ120BG device.

- Ultrafast recovery times
- Soft recovery characteristics
- Low forward voltage
- Low leakage current
- Avalanche energy rated
- RoHS compliant
- AEC-Q101 qualified

### 2.2 Benefits

The following are benefits of the APT15DQ120BG device.

- Low switching losses
- Low noise (EMI) switching
- Cooler operation
- Higher reliability systems
- Increased system power density

### 2.3 Applications

The APT15DQ120BG device is designed for the following applications.

- Power factor correction (PFC)
- Anti-parallel diode
  - Switch-mode power supply
  - Inverters/converters
- Freewheeling diode
  - Inverters/converters
  - Motor controllers
- Snubber/clamp diode

### 3 Electrical Specifications

This section shows the electrical specifications for the APT15DQ120BG device.

#### 3.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the APT15DQ120BG device.

All ratings:  $T_c = 25\text{ }^\circ\text{C}$  unless otherwise specified.

**Table 1 • Absolute Maximum Ratings**

Symbol	Parameter	Ratings	Unit
$V_R$	Maximum DC reverse voltage	1200	V
$V_{RRM}$	Maximum peak repetitive reverse voltage	1200	
$V_{RWM}$	Maximum working peak reverse voltage	1200	
$I_{F(AV)}$	Maximum average forward current ( $T_c = 127\text{ }^\circ\text{C}$ , duty cycle = 0.5)	15	A
$I_{F(RMS)}$	RMS forward current (Square wave, 50% duty)	29	
$I_{FSM}$	Non-repetitive forward surge current ( $T_j = 45\text{ }^\circ\text{C}$ , 8.3 ms)	110	
$E_{AVL}$	Avalanche energy (1 A, 40 mH)	20	mJ
$T_j, T_{STG}$	Operating and storage temperature range	-55 to 175	$^\circ\text{C}$
$T_L$	Lead temperature for 10 seconds	300	

The following table shows the thermal and mechanical characteristics of the APT15DQ120BG device.

**Table 2 • Thermal and Mechanical Characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance			1.18	$^\circ\text{C}/\text{W}$
$W_t$	Package weight		0.22		oz
			6.2		g
	Maximum mounting torque			10	lbf-in
				1.1	N-m

#### 3.2 Electrical Performance

The following table shows the static electrical characteristics of the APT15DQ120BG device.

**Table 3 • Static Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_F$	Forward voltage	$I_F = 15\text{ A}$		2.8	3.3	V
		$I_F = 30\text{ A}$		3.4		
		$I_F = 15\text{ A}, T_j = 125\text{ }^\circ\text{C}$		2.5		
$I_{RM}$	Maximum reverse leakage current	$V_R = 1200\text{ V}$			100	$\mu\text{A}$
		$V_R = 1200\text{ V}, T_j = 125\text{ }^\circ\text{C}$			500	
$C_j$	Junction capacitance	$V_R = 200\text{ V}$		17		pF

### 3.3 Dynamic Characteristics

The following table shows the dynamic characteristics of the APT15DQ120BG device.

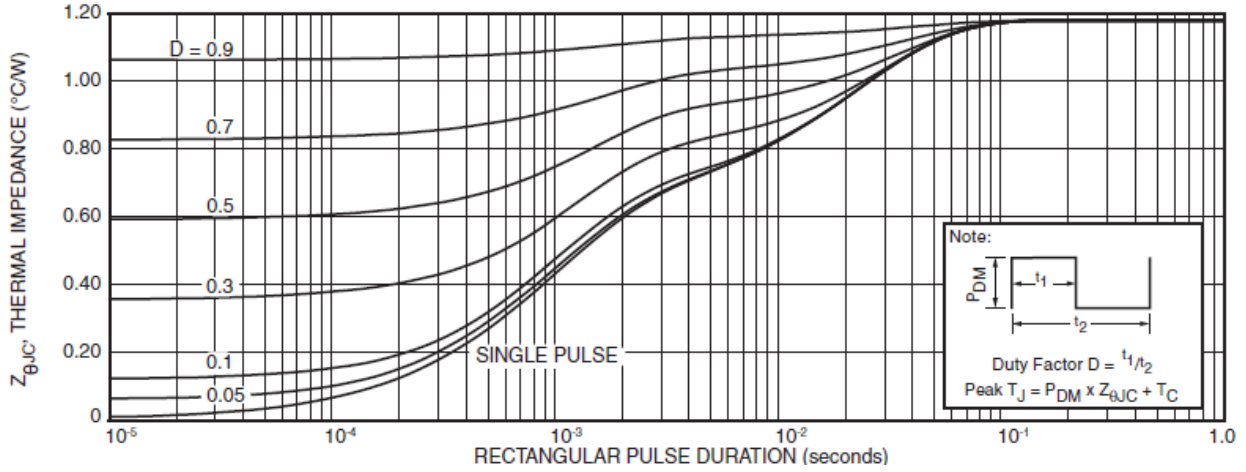
**Table 4 • Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$t_{rr}$	Reverse recovery time	$I_F = 1\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$ $T_J = 25\text{ }^\circ\text{C}$		21		ns
$t_{rr}$	Reverse recovery time	$I_F = 15\text{ A}$		240		
$Q_{rr}$	Reverse recovery charge	$di_F/dt = -200\text{ A}/\mu\text{s}$ $V_R = 800\text{ V}$		260		nC
$I_{RRM}$	Maximum reverse recovery current	$T_C = 25\text{ }^\circ\text{C}$		3		A
$t_{rr}$	Reverse recovery time	$I_F = 15\text{ A}$		290		ns
$Q_{rr}$	Reverse recovery charge	$di_F/dt = -200\text{ A}/\mu\text{s}$ $V_R = 800\text{ V}$		960		nC
$I_{RRM}$	Maximum reverse recovery current	$T_C = 125\text{ }^\circ\text{C}$		6		A
$t_{rr}$	Reverse recovery time	$I_F = 15\text{ A}$		130		ns
$Q_{rr}$	Reverse recovery charge	$di_F/dt = -1000\text{ A}/\mu\text{s}$ $V_R = 800\text{ V}$		1340		nC
$I_{RRM}$	Maximum reverse recovery current	$T_C = 125\text{ }^\circ\text{C}$		19		A

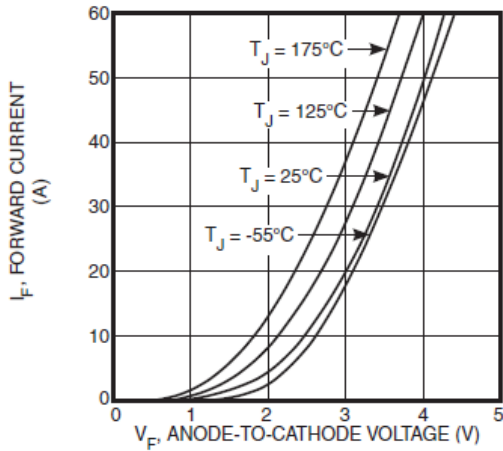
### 3.4 Typical Performance Curves

This section shows the typical performance curves for the APT15DQ120BG device.

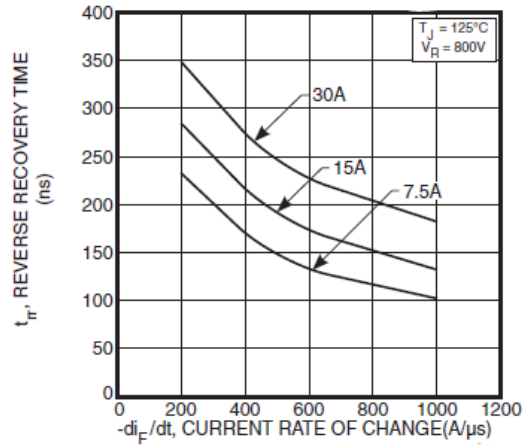
**Figure 1 • Maximum Effective Transient Thermal Impedance, Junction-To-Case vs. Pulse Duration**



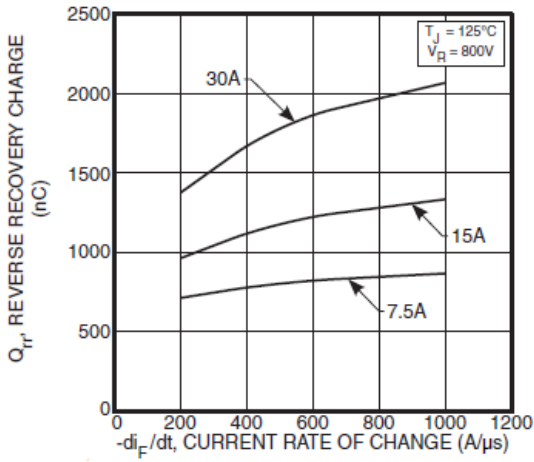
**Figure 2 • Forward Current vs. Forward Voltage**



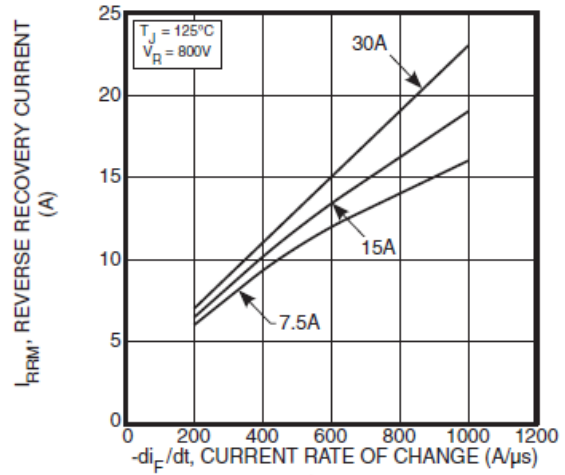
**Figure 3 • RRT vs. Current Rate of Change**



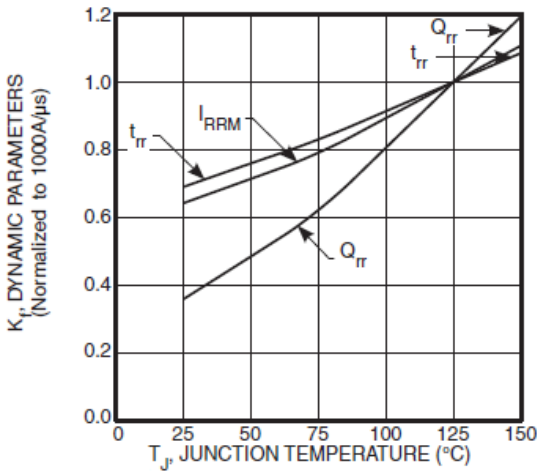
**Figure 4 • Reverse Recovery Charge vs. Current Rate of Change**



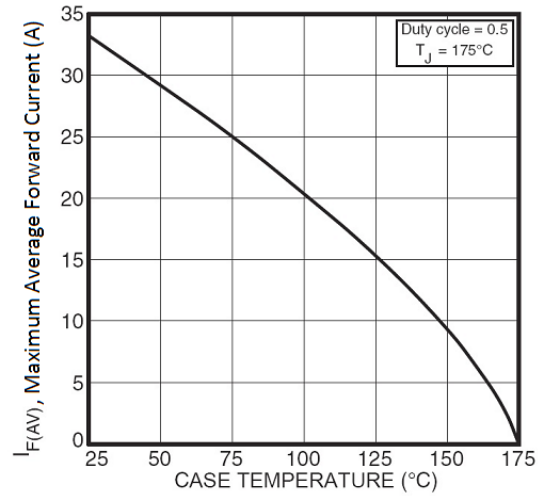
**Figure 5 • Reverse Recovery Current vs. Current Rate of Change**



**Figure 6 • Dynamic Parameters vs. Junction Temperature**

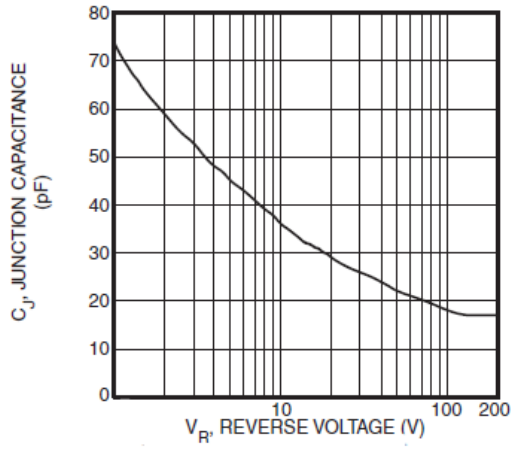


**Figure 7 • Maximum Average Forward Current vs. Case Temperature**





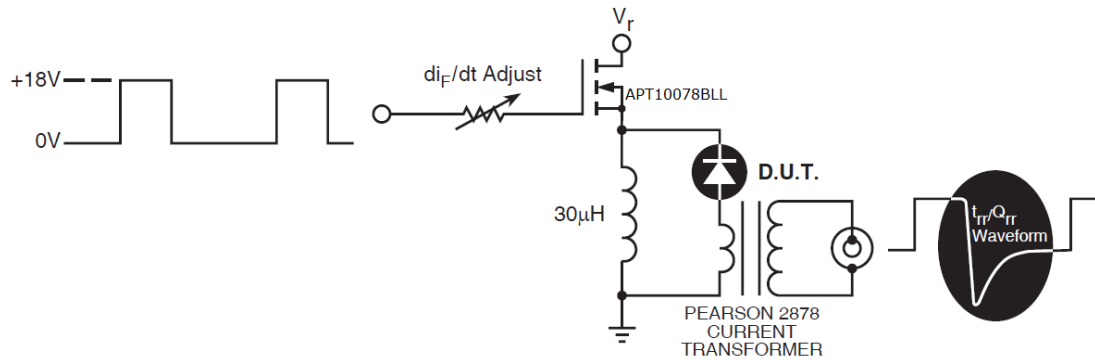
**Figure 8 • Junction Capacitance vs. Reverse Voltage**



### 3.5 Reverse Recovery Overview

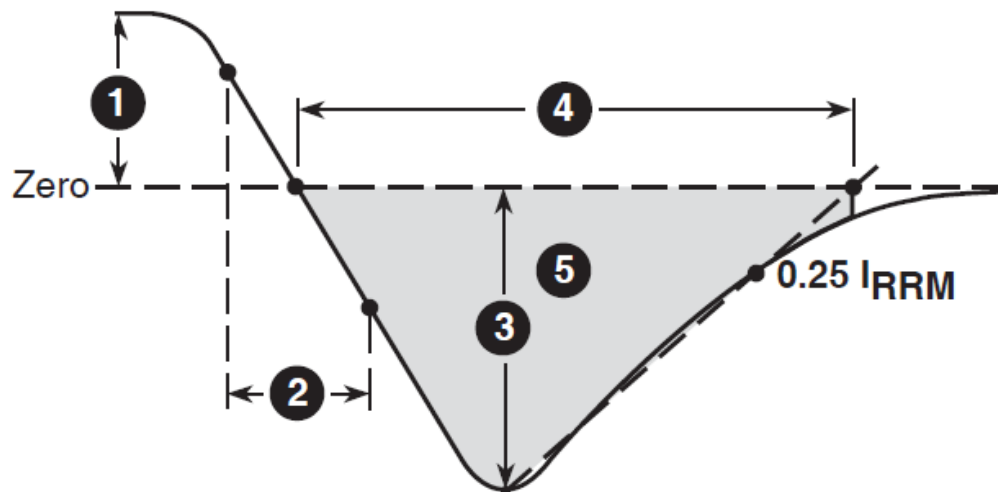
The following illustration shows the diode test circuit for the APT15DQ120BG device.

Figure 9 • Diode Test Circuit



The following illustration shows the diode reverse recovery waveform and definitions for the APT15DQ120BG device.

Figure 10 • Diode Reverse Recovery Waveform and Definitions



1. I<sub>F</sub>—Forward conduction current.
2. di<sub>F</sub>/dt—Rate of diode current change through zero crossing.
3. I<sub>RRM</sub>—Maximum reverse recovery current.
4. t<sub>rr</sub>—Reverse recovery time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I<sub>RRM</sub> and 0.25 • I<sub>RRM</sub> passes through zero.
5. Q<sub>rr</sub>—Area under the curve defined by I<sub>RRM</sub> and t<sub>rr</sub>.

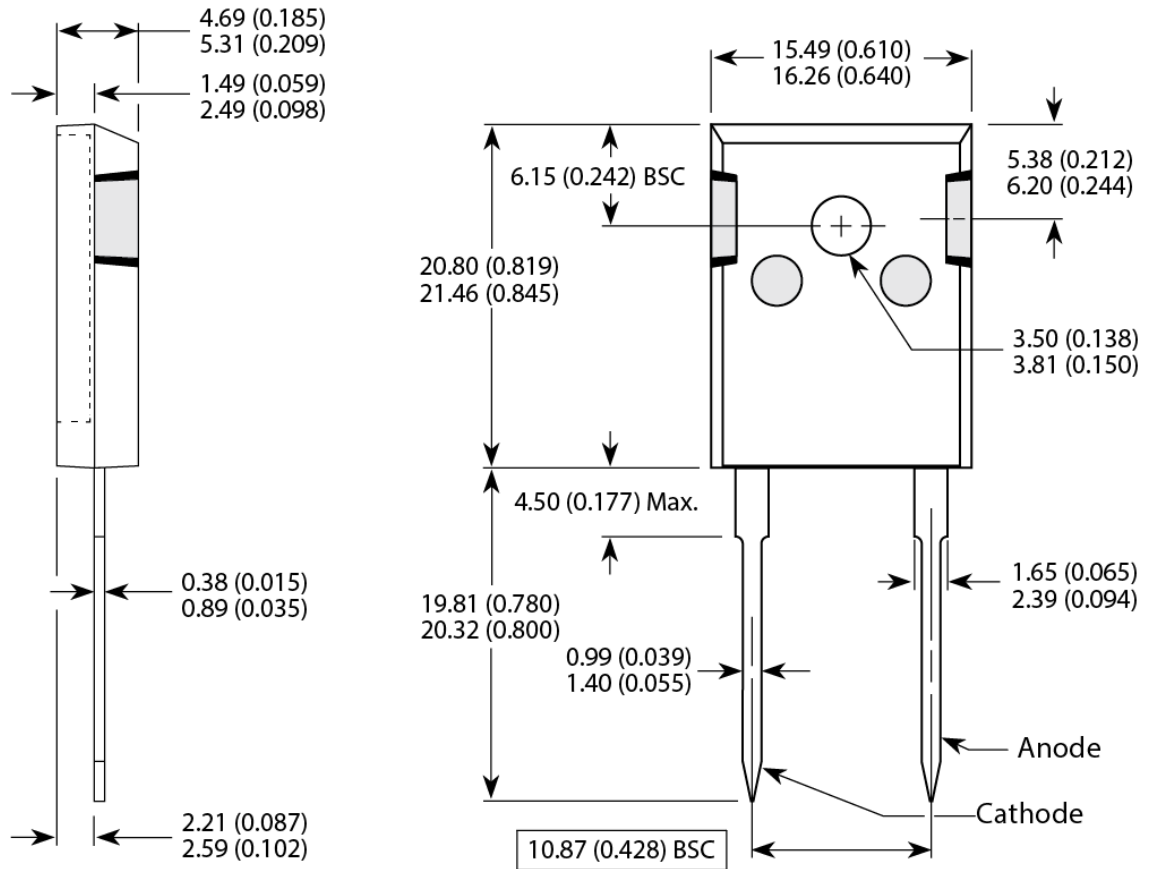
## 4 Package Specification

This section shows the package specification for the APT15DQ120BG device.

### 4.1 Package Outline Drawing

This section shows the TO-247 package drawing of the APT15DQ120BG device. Dimensions are in millimeters and (inches).

Figure 11 • TO-247 Package Outline



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